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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Serial No.: 10/647,714

Conf. No.: 2476

Filing Date: 08/25/2003

Art Unit: 2818

Applicant: Khan et al.

Examiner: Le, Thao P.

Title: METAL OXIDE SEMICONDUCTOR
HETEROSTRUCTURE FIELD EFFECT
TRANSISTOR

Docket No.: SETI-0002DIV

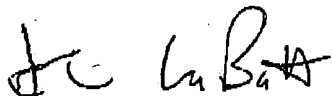
COMMISSIONER FOR PATENTS

DESTINATION PHONE NUMBER: 703-872-9306

Transmitted herewith is: Amendment in 11 pages

in the above identified application.

- ☒ No additional fee is required.
- ☒ The Commissioner is hereby authorized to charge and credit Deposit Account No. 500999 as described below.
- ☒ Credit any overpayment.
- ☒ Charge any additional fee required.



John W. LaBatt, Reg. No. 48,301

DATE: May 25, 2004

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Mail Stop Amendment
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

AMENDMENT

Sir:

This paper is being filed in response to the Office Action dated March 11, 2004. Please amend the above-identified application as follows:

Amendments to the Claims are reflected in the listing of claims that begins on page 2 of this paper.

Remarks begin on page 7 of this paper.

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